

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2933	(resistor or resistive or intrinsic near silicon or intrinsic near si or i-Si or refractory near metal near sin or refractory near metal near silicon near nitride or WSiN or tasin or tisin or microcrystalline near si or amorphous near si or microcrystalline near silicon or amorphous near silicon) near10 (antifuse or anti-fuse or voltage near breakdown or rupturing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 09:17
L2	266	(resistor or resistive or intrinsic near silicon or intrinsic near si or i-Si or refractory near metal near sin or refractory near metal near silicon near nitride or WSiN or tasin or tisin or microcrystalline near si or amorphous near si or microcrystalline near silicon or amorphous near silicon) near10 (antifuse or anti-fuse or voltage near breakdown or rupturing) near10 (series or serial or stacked or "adjacent")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 10:22
L3	36	(resistor or resistive or intrinsic near silicon or intrinsic near si or i-Si or refractory near metal near sin or refractory near metal near silicon near nitride or WSiN or tasin or tisin or microcrystalline near si or amorphous near si or microcrystalline near silicon or amorphous near silicon) near10 (antifuse or anti-fuse or voltage near breakdown or rupturing) near10 (series or serial or stacked or "adjacent") and ((row or column or bit or digit or word or address or addressing or select or selection or selecting) near2 (line or conductor or conducting) or wordline or bitline or digitline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 10:55

## EAST Search History

L4	91	(resistor or resistive or intrinsic near silicon or intrinsic near si or i-Si or refractory near metal near sin or refractory near metal near silicon near nitride or WSiN or tasin or tisin or microcrystalline near si or amorphous near si or microcrystalline near silicon or amorphous near silicon) near10 (antifuse or anti-fuse or voltage near breakdown or rupturing) same ((row or column or bit or digit or word or address or addressing or select or selection or selecting) near2 (line or conductor or conducting) or wordline or bitline or digitline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 12:37
L5	2868	(resistor or linear\$2 near resist\$4) near6 ((row or column or bit or digit or word or address or addressing or select or selection or selecting) near2 (line or conductor or conducting) or wordline or bitline or digitline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 12:38
L6	194	(resistor or linear\$2 near resist\$4) near6 ((row or column or bit or digit or word or address or addressing or select or selection or selecting) near2 (line or conductor or conducting) or wordline or bitline or digitline) and (antifus\$4 or anti-fus\$4 or voltage near breakdown)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 13:02
L7	21	(resistor or linear\$2 near resist\$4) near4 (antifus\$4 or anti-fus\$4 or voltage near breakdown) near4 (series or serial) and ((row or column or bit or digit or word or address or addressing or select or selection or selecting) near2 (line or conductor or conducting) or wordline or bitline or digitline or otp or worm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 13:05
L8	36	(brocklin.in.) and (resist\$3) near20 (antifus\$3 or anti-fus\$4 or voltage near breakdown)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 13:07

## EAST Search History

L9	18	(US-20030081445-\$ or US-20030062590-\$ or US-20020074616-\$ or US-20020136076-\$).did. or (US-6570795-\$ or US-6549458-\$ or US-6483736-\$ or US-6051851-\$ or US-6541792-\$ or US-6448576-\$ or US-RE36893-\$ or US-5770885-\$ or US-4903111-\$ or US-6532170-\$ or US-6515888-\$ or US-3582908-\$ or US-6525953-\$).did. or (US-20030132458-\$).did.	US-PGPUB; USPAT; DERWENT	OR	ON	2006/06/20 13:27
L10	4	"5714416".pn. "5726484".pn.	US-PGPUB; USPAT; DERWENT	OR	ON	2006/06/20 13:27
L11	2	("5714416").URPN.	USPAT	OR	ON	2006/06/20 13:40
L12	3	("5166901"   "5353246"   "5440167"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/20 13:56
L15	6	"5856775".pn. "20010055838" "5070383".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 14:05
L17	1137	365/225.7.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 15:03
L18	321	365/225.7.ccls. and (resistor or linear\$2 near resist\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 14:52
L19	327	438/598.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 14:52
L20	4703	257/E27.103.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 15:03

## EAST Search History

L21	521	257/E27.103.ccls. and (antifus\$3 or anti-fus\$3 or voltage near breakdown or ruptur\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 15:04
L22	25	257/E27.103.ccls. and (antifus\$3 or anti-fus\$3 or voltage near breakdown or ruptur\$3) near10 (resistor or resistance or resistive)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 15:05
S44	372	(worm or write adj once or otp or once near2 programmable or one near2 programmable) and (switch or antifuse or anti-fuse or shorting or short or antifusing or anti-fusing or voltage near3 breakdown) and (linear or linearly or ideal) near4 (resistor or resistive or resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 13:05
S45	193	(worm or write adj once or otp or once near2 programmable or one near time near programmable) and (switch or antifuse or anti-fuse or shorting or short or antifusing or anti-fusing or voltage near3 breakdown) and (linear or linearly or ideal) near4 (resistor or resistive or resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 13:34
S46	75	memory and (state adj change) and steering with (resistor or resistive or resistance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 13:49
S47	265	257/50.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 14:16
S48	433	257/209.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 15:01
S49	917	257/529.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 15:39

## EAST Search History

S50	689	257/530.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 15:39
S51	15	(US-20030081445-\$ or US-20030062590-\$).did. or (US-4903111-\$ or US-6570795-\$ or US-6549458-\$ or US-6541792-\$ or US-6532170-\$ or US-6525953-\$ or US-6515888-\$ or US-6483736-\$ or US-RE36893-\$ or US-5770885-\$ or US-6448576-\$ or US-6051851-\$ or US-3582908-\$).did.	US-PGPUB; USPAT	OR	ON	2006/06/19 15:54
S52	249	438/131.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 16:10
S53	372	438/132.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 16:25
S54	241	438/467.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 16:39
S55	276	438/600.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 16:39
S56	159	(worm or write adj once or otp or one adj time adj programm\$) and (antifuse or antifusing or anti-fuse or anti-fusing) and (digital adj camera or memory adj card)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 16:58
S57	52	(memory or otp or worm or eeprom or prom or storage or (row or column) near3 (conductor or line)) and (antifuse or antifusing or anti-fuse or anti-fusing or voltage near breakdown) near6 (alumina or aluminum adj oxide or al near2 o or al2o3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 17:10

## EAST Search History

S58	74	(antifuse or antifusing or anti-fuse or anti-fusing) and (memory or prom or eeprom) and (resistor or resistive) with (intrinsic adj silicon or amorphous adj silicon or lightly adj doped near2 silicon or microcrystalline adj silicon or refractory adj metal adj silicon or tungsten adj silicon adj nitride) and (bit or word or digit or (column or row) near4 (conductor or conductive or line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/19 17:14
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# Interference Text Search

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L23	112	((row or column or digit or word or bit or select or selection or address or addressing) near (line or conductor or conducting) or bitline or digitline or wordline) near6 (antifus\$3 or anti-fus\$4 or voltage near breakdown or tunnel near junction or tunneling or rupturing or voltage near2 ruptur\$3)).clm.	US-PGPUB	OR	ON	2006/06/20 15:13
L25	2	((row or column or digit or word or bit or select or selection or address or addressing) near (line or conductor or conducting) or bitline or digitline or wordline) and (antifus\$3 or anti-fus\$4 or voltage near breakdown or tunnel near junction or tunneling or rupturing or voltage near2 ruptur\$3) near8 (blanket\$4 or unpattern\$4 or non-pattern\$4 or "not" near pattern\$4)).clm.	US-PGPUB	OR	ON	2006/06/20 15:14
L26	65	((row or column or digit or word or bit or select or selection or address or addressing) near (line or conductor or conducting) or bitline or digitline or wordline) and (antifus\$3 or anti-fus\$4 or voltage near breakdown or tunnel near junction or tunneling or rupturing or voltage near2 ruptur\$3) near8 (resistor or resistance or resistive)).clm.	US-PGPUB	OR	ON	2006/06/20 15:15
L28	9	((rom or prom or otp or worm or eeprom or eeprom or programmable near3 memory) and (antifus\$3 or anti-fus\$4 or voltage near breakdown or tunnel near junction or tunneling or rupturing or voltage near2 ruptur\$3) near8 (resistor or resistance or resistive)).clm.	US-PGPUB	OR	ON	2006/06/20 15:18
L29	0	((memory near cell) same (antifus\$3 or anti-fus\$3 or tunnel near junction or tunneling or voltage near breakdown or rupturing or rupture) same (linear\$4 near resist\$4)).clm.	US-PGPUB	OR	ON	2006/06/20 15:18

**Scharpen, Debbie K**

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**From:** Myers, Tim (Legal - Corvallis)  
**Sent:** Tuesday, June 20, 2006 12:47 PM  
**To:** Scharpen, Debbie K  
**Subject:** 10012761-5

**CustomSentDate:** 6/20/2006 12:46:53 PM

Hi Debbie, This case has transferred to Don Coulman but I was responsible for it. I got a call from the Examiner who said the abstract is missing in their files but it appears that they did receive it. She wanted our confirmation of what it was. It was:

A memory structure has a plurality of row conductors intersecting a plurality of column conductors at a plurality of intersections. Each intersection includes an electrically linear resistive element in series with a voltage breakdown element.

Could you please fax this abstract to Examiner Jennifer Dolan at 571-273-1690 (fax) today? Thanks. Her phone no. is 571-272-1690 (slight different in prefix) if there are any questions. Thanks again - Tim

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